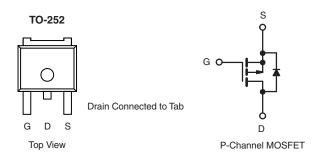
**Vishay Siliconix** 



## Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.013			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.022			
I <sub>D</sub> (A)	- 50			
Configuration	Single			



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21
   Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>
- Find out more about Vishay's Automotive Grade Product Requirements at: <a href="http://www.vishay.com/applications">www.vishay.com/applications</a>



 ORDERING INFORMATION

 Package
 TO-252

 Lead (Pb)-free and Halogen-free
 SQD50P04-13L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current	$T_C = 25 \ ^{\circ}C^a$	- I <sub>D</sub>	- 50		
	T <sub>C</sub> = 125 °C		- 35		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 39		
Single Pulse Avalanche Energy		E <sub>AS</sub>	76	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	PD	83	W	
	T <sub>C</sub> = 125 °C		27	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.8	0/10

#### Notes

a. Package limited.

- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = -250 \mu A$		- 40	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-	- 2.5		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V	-	-	- 1		
	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA	
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A	-	0.010	0.013	Ω	
Drain Course On State Registeres	P	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 125 °C	-	-	0.019		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 175 °C	-	-	0.023		
		$V_{GS} = -4.5 V$	I <sub>D</sub> = - 14 A	-	0.016	0.022		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> =	- 15 V, I <sub>D</sub> = - 17 A	-	38	-	S	
Dynamic <sup>b</sup>		<u>.</u>						
Input Capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V V <sub>DS</sub> = - 20 V, f = 1 MHz	-	2872	3590	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	508	635		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	352	440	1	
Total Gate Charge <sup>c</sup>	Qg	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> = - 40 V, I <sub>D</sub> = - 50 A	-	60	90		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	5.7	8.6	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	14.7	22		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = - 20 \text{ V}, \text{ R}_{\text{L}} = 0.4 \Omega$ $\text{I}_{\text{D}} \cong -50 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	12	18	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	40	60		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 35 A, V <sub>GS</sub> = 0 V		-	- 0.9	- 1.5	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

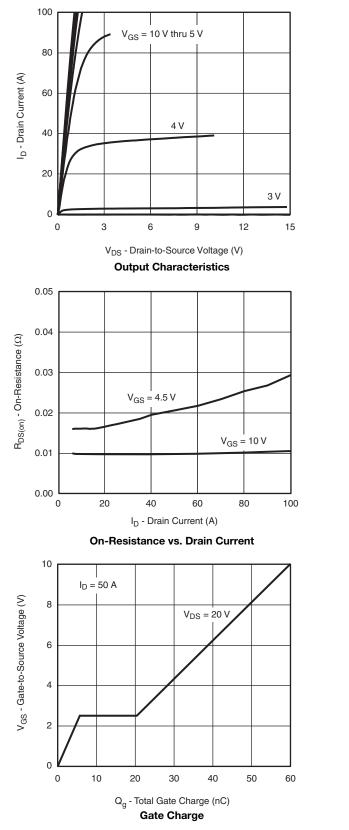
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

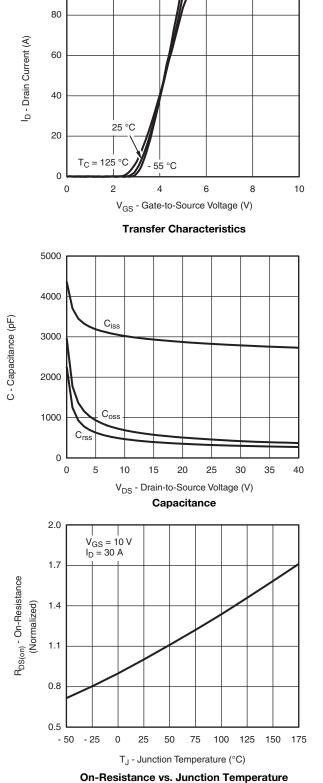
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

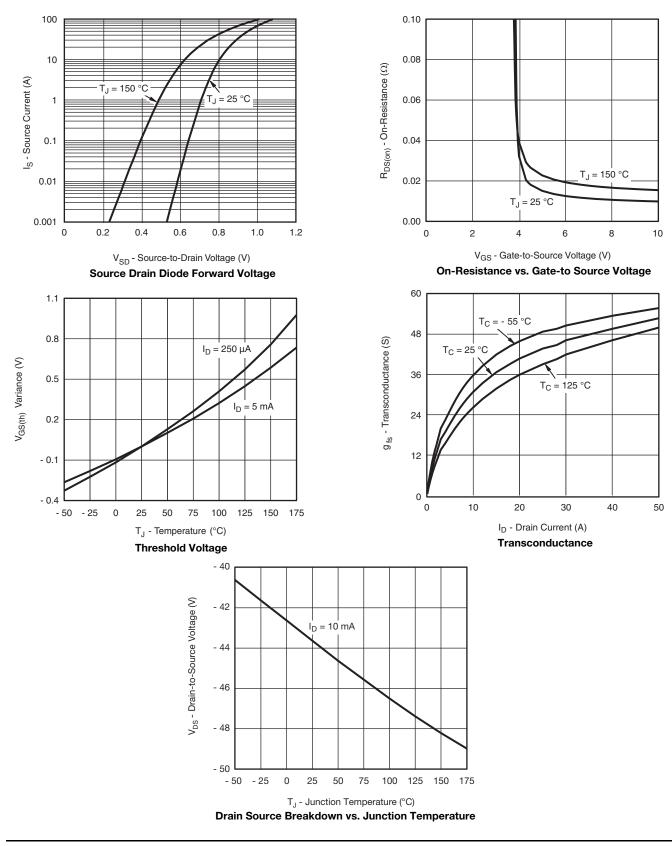


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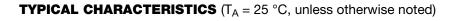


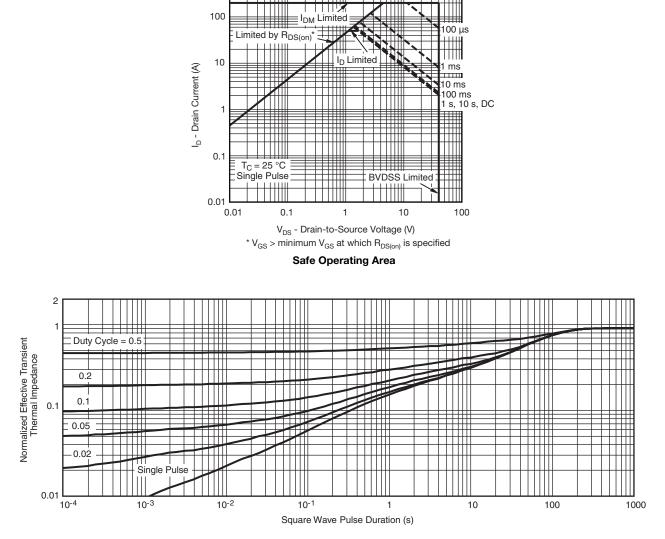


#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



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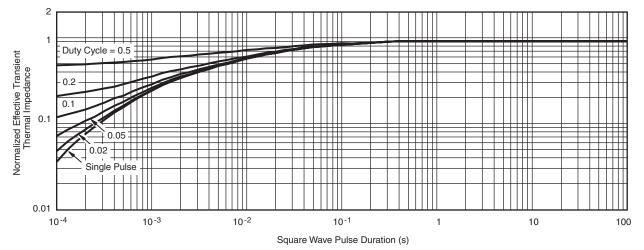


Normalized Thermal Transient Impedance, Junction-to-Ambient

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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65157">www.vishay.com/ppg?65157</a>.



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